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AFT 84.1001

What is claimed is:

1. A Group III nitride semiconductor light-emitting element including an n-type contact layer of n-type GaN, an n-type clad layer of n-type $\text{Al}_x\text{Ga}_{1-x-y}\text{In}_y\text{N}$ ($0 < x < 1$, $0 \leq y < 1$,
5 $0 < x+y < 1$), an active layer, a p-type clad layer, and a p-type contact layer, comprising:
a crack-preventing layer of n-type GaN provided between the n-type contact layer and the n-type clad layer,
wherein the crack-preventing layer has a dopant
10 concentration lower than that of the n-type contact layer.
2. The light-emitting element according to claim 1, wherein the crack-preventing layer has a dopant concentration lower than $4 \times 10^{18} \text{ cm}^{-3}$.
3. The light-emitting element according to claim 2,
15 wherein the crack-preventing layer has a dopant concentration within a range of $5 \times 10^{16} \text{ cm}^{-3}$ to $5 \times 10^{17} \text{ cm}^{-3}$.
4. The light-emitting element according to claim 1, wherein the n-type contact layer has a dopant concentration within a range of $4 \times 10^{18} \text{ cm}^{-3}$ to $2 \times 10^{19} \text{ cm}^{-3}$.
- 20 5. The light-emitting element according to claim 1, wherein a dopant of the crack-preventing layer is either one of Si and Ge.
6. The light-emitting element according to claim 1, wherein a dopant of the n-type contact layer is either one
25 of Si and Ge.
7. A method of manufacturing a semiconductor light-emitting element having a multilayered structure

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constituted by sequentially stacking layers of Group III nitride semiconductors one upon another on a substrate, the method comprising:

an n-type contact-layer forming step of forming an n-
5 type contact layer of n-type GaN, and

a crack-preventing layer forming step of forming a crack-preventing layer of n-type GaN, the crack-preventing layer having a dopant concentration lower than that of the n-type contact layer.

10 8. The method according to claim 7, wherein the crack-preventing layer forming step includes a step of reducing an amount of supply of a dopant material used in the n-type contact-layer forming step.